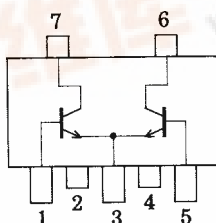


SANYO**FP209**

NPN Epitaxial Planar Silicon Transistor

Driver Applications**Features**

- Composite type with 2 transistors (NPN) contained in one package, facilitating high-density mounting.
- The FP209 is formed with 2 chips being equivalent to the 2SD1621, placed in one package.

Electrical Connection

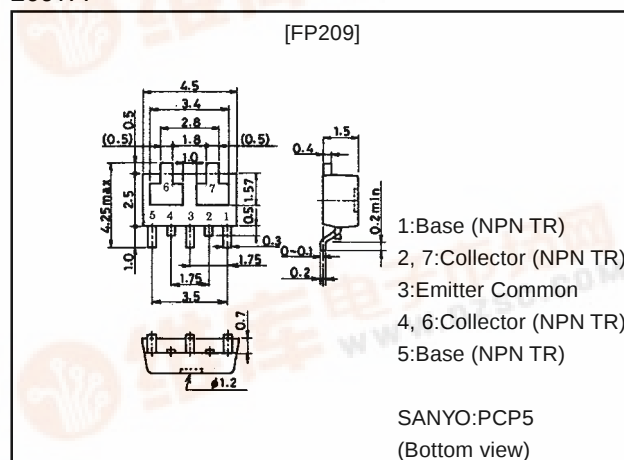
- 1:Base (NPN TR)
2, 7:Collector (NPN TR)
3:Emitter Common
4, 6:Collector (NPN TR)
5:Base (NPN TR)

(Top view)

Package Dimensions

unit:mm

2097A



- 1:Base (NPN TR)
2, 7:Collector (NPN TR)
3:Emitter Common
4, 6:Collector (NPN TR)
5:Base (NPN TR)

SANYO:PCP5
(Bottom view)

Specifications**Absolute Maximum Ratings at Ta = 25°C**

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CB0}		30	V
Collector-to-Emitter Voltage	V_{CEO}		25	V
Emitter-to-Base Voltage	V_{EBO}		6	V
Collector Current	I_C		2	A
Collector Current (Pulse)	I_{CP}		5	A
Base Current	I_B		400	mA
Collector Dissipation	P_C	Mounted on ceramic board (250mm ² ×0.8mm) 1unit	0.8	W
Total Dissipation	P_T	Mounted on ceramic board (250mm ² ×0.8mm)	1.1	W
Junction Temperature	T_J		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

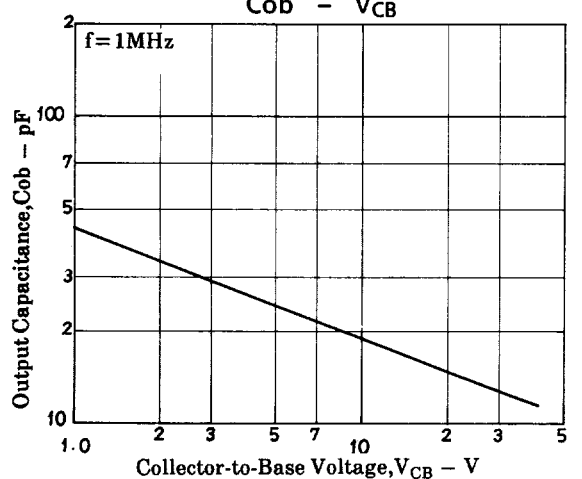
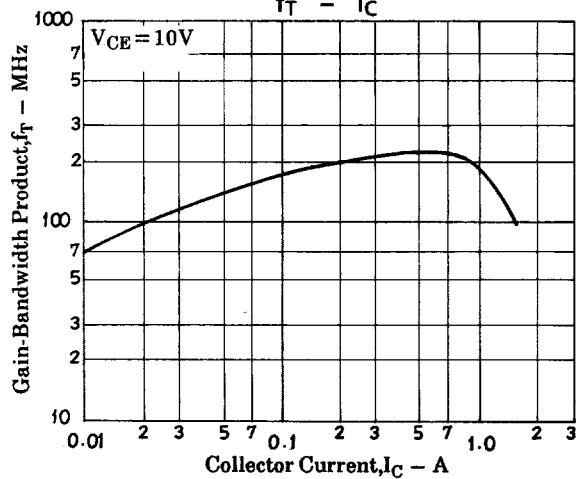
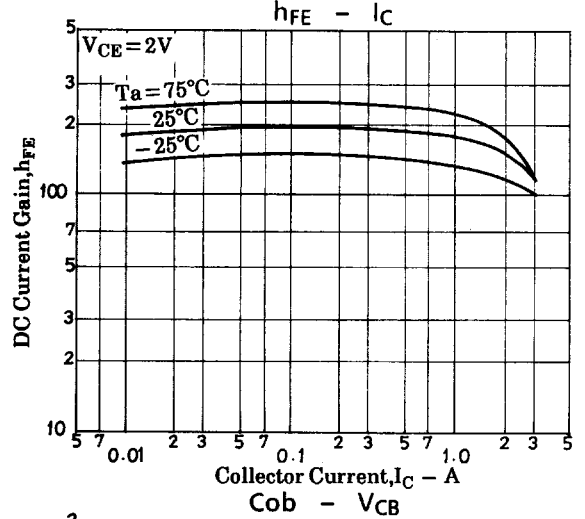
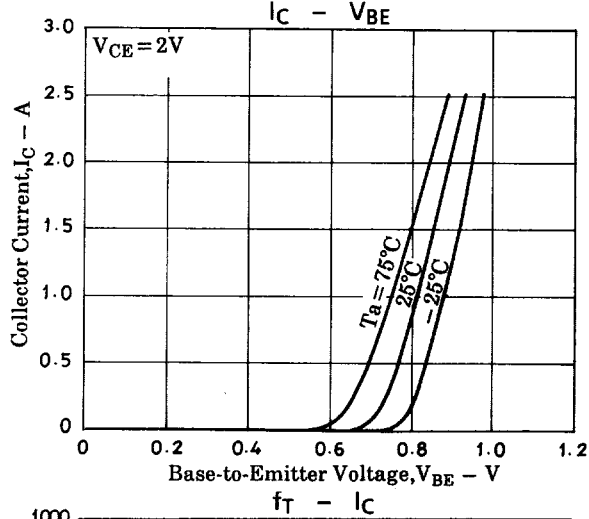
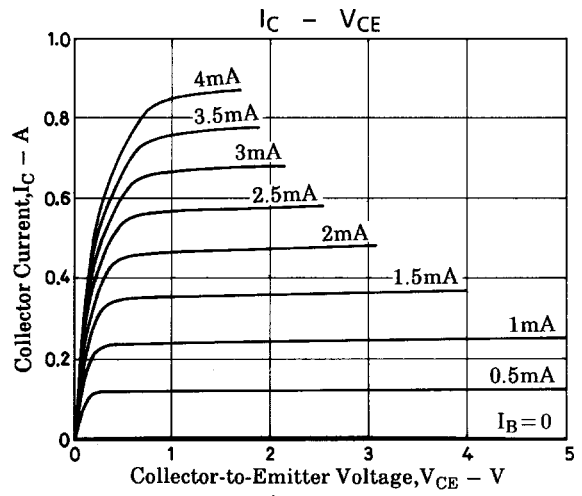
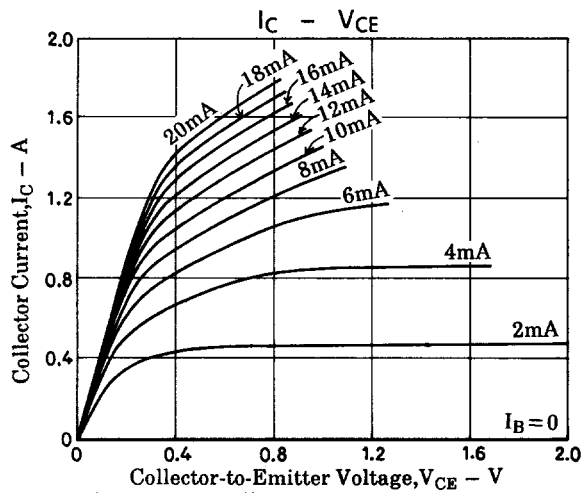
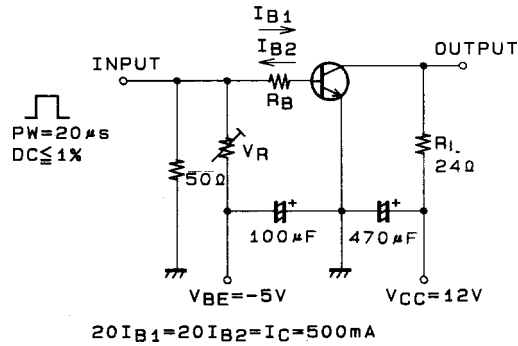
Electrical Characteristics at Ta=25°C

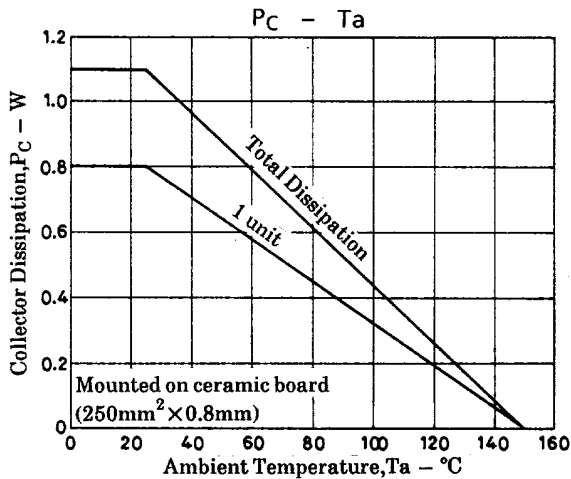
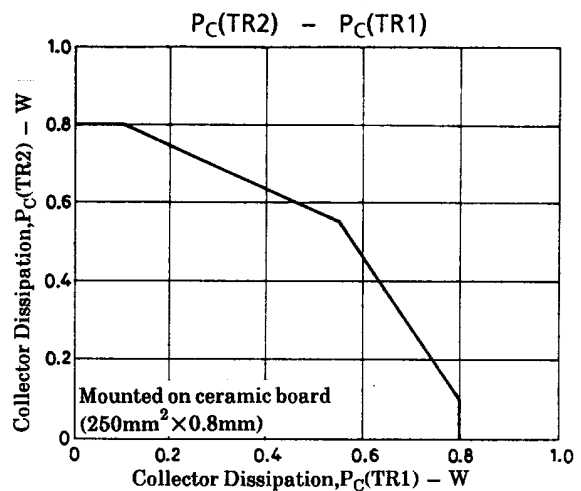
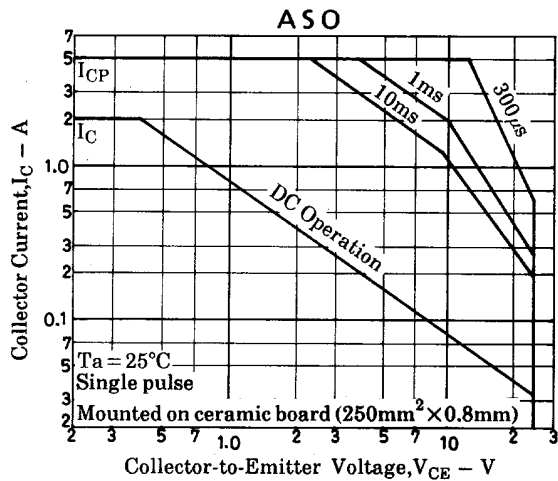
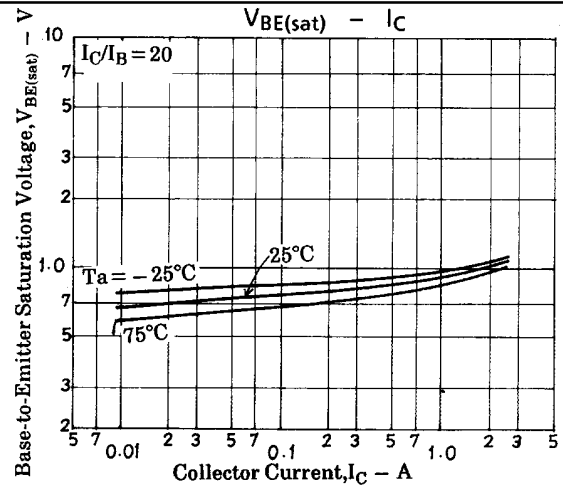
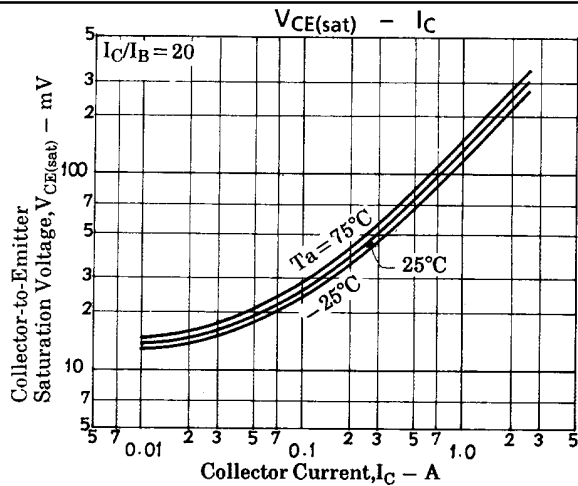
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=20V, I_E=0$			100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=4V, I_C=0$			100	nA
DC Current Gain	h_{FE}	$V_{CE}=2V, I_C=100mA$	140		400	
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=50mA$		150		MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, f=1MHz$		19		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=1.5A, I_B=75mA$		0.18	0.4	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=1.5A, I_B=75mA$		0.85	1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	30			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	25			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Turn-ON Time	t_{on}	See specified Test Circuit		60		ns
Storage Time	t_{stg}	See specified Test Circuit		500		ns
Fall Time	t_f	See specified Test Circuit		25		ns

Marking:209



Switching Time Test Circuit





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